## 1N4148-K

## SILICON EPITAXIAL PLANAR DIODE

Fast switching diode

This diode is also available in MiniMELF case with the type designation LL4148.


Glass Case DO-35 (K)
Dimensions in mm

Absolute Maximum Ratings $\left(\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}\right)$

| Parameter | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Peak Reverse Voltage | $\mathrm{V}_{\mathrm{RM}}$ | 100 | V |
| Reverse Voltage | $\mathrm{V}_{\mathrm{R}}$ | 75 | V |
| Average Rectified Forward Current | $\mathrm{I}_{\mathrm{F}(\mathrm{AV})}$ | 200 | mA |
| Non-repetitive Peak Forward Surge Currentat $\mathrm{t}=1 \mathrm{~s}$ <br> at $\mathrm{t}=1 \mathrm{~ms}$ <br> at $=1 \mu \mathrm{~s}$ | $\mathrm{I}_{\mathrm{FSM}}$ | 0.5 |  |
| Power Dissipation |  | 1 | A |
| Junction Temperature | $\mathrm{P}_{\text {tot }}$ | $500{ }^{1)}$ | mW |
| Storage Temperature Range | $\mathrm{T}_{\mathrm{j}}$ | 200 | ${ }^{\circ} \mathrm{C}$ |

${ }^{1)}$ Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

Characteristics at $\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$

| Parameter | Symbol | Min. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: |
| Forward Voltage at $I_{F}=10 \mathrm{~mA}$ | $V_{F}$ | - | 1 | V |
| $\begin{aligned} & \text { Leakage Current } \\ & \text { at } V_{R}=20 \mathrm{~V} \\ & \text { at } \mathrm{V}_{R}=75 \mathrm{~V} \\ & \text { at } \mathrm{V}_{\mathrm{R}}=20 \mathrm{~V}, \mathrm{~T}_{\mathrm{j}}=150^{\circ} \mathrm{C} \end{aligned}$ | $\begin{aligned} & \mathrm{I}_{\mathrm{R}} \\ & \mathrm{I}_{\mathrm{R}} \\ & \mathrm{I}_{\mathrm{l}} \end{aligned}$ | - | $\begin{gathered} 200 \\ 5 \\ 50 \\ \hline \end{gathered}$ | nA <br> $\mu \mathrm{A}$ <br> $\mu \mathrm{A}$ |
| Reverse Breakdown Voltage at $I_{R}=100 \mu \mathrm{~A}$ at $\mathrm{I}_{\mathrm{R}}=5 \mu \mathrm{~A}$ | $V_{\text {(BR)R }}$ <br> $V_{\text {(BR)R }}$ | $\begin{gathered} 100 \\ 75 \end{gathered}$ | - | $\begin{aligned} & V \\ & V \end{aligned}$ |
| Capacitance at $\mathrm{V}_{\mathrm{F}}=\mathrm{V}_{\mathrm{R}}=0$ | $\mathrm{C}_{\text {tot }}$ | - | 4 | pF |
| Voltage Rise when Switching ON tested with 50 mA Forward Pulses $\mathrm{tp}=0.1 \mathrm{~s}$, Rise Time $<30 \mathrm{~ns}, \mathrm{fp}=5$ to 100 KHz | $\mathrm{V}_{\mathrm{fr}}$ | - | 2.5 | V |
| Reverse Recovery Time from $I_{F}=10 \mathrm{~mA}$ to $\mathrm{I}_{\mathrm{R}}=1 \mathrm{~mA}, \mathrm{~V}_{\mathrm{R}}=6 \mathrm{~V}, \mathrm{R}_{\mathrm{L}}=100 \Omega$ | $t_{\text {rr }}$ | - | 4 | ns |
| Thermal Resistance Junction to Ambient Air | $\mathrm{R}_{\text {thA }}$ | - | $0.35{ }^{1)}$ | K/mW |
| Rectification Efficiency at $\mathrm{f}=100 \mathrm{MHz}, \mathrm{V}_{\mathrm{RF}}=2 \mathrm{~V}$ | $\eta_{v}$ | 0.45 | - | - |

${ }^{1)}$ Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.


Rectification Efficiency Measurement Circuit







